

1. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of from $\sim 6 \times 10^{19} \text{ cm}^{-3}$ to $\sim 3.75 \times 10^{20} \text{ cm}^{-3}$.

2. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of less than $\sim 3.75 \times 10^{20} \text{ cm}^{-3}$.

11. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of greater than $\sim 6 \times 10^{19} \text{ cm}^{-3}$.

12. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a late implant doping technique.